FRANC

ELECTRONICS

& MTO Symposium

Background

GOAL: Develop **faster** and more **efficient** machine learning accelerators using arrays of **emerging analog devices** called resistive switches (ReRAM) and **digital coprocessors**

CONTEXT: ReRAM technology promise **100-10,000x** lower energy consumption, **30,000x** faster operation than SOA.

PROBLEM: High write energy, high write latency, limited endurance, non-ideal weight updates, limited digital coprocessor resources

CURRENT SOLUTIONS: 1) Find better devices \rightarrow will always be imperfect 2) **Batch training** [1] + duplicate memory + 1-by-1 device programming (**Fig. 1a**, [2]) \rightarrow requires expensive coprocessor or emerging technology

OUR VISION: Low-rank coprocessor for **batch training** in conventional hardware (systolic arrays [3]) to extract and use only most important information during training (**Fig. 1b**)

+ high performance, memory efficient



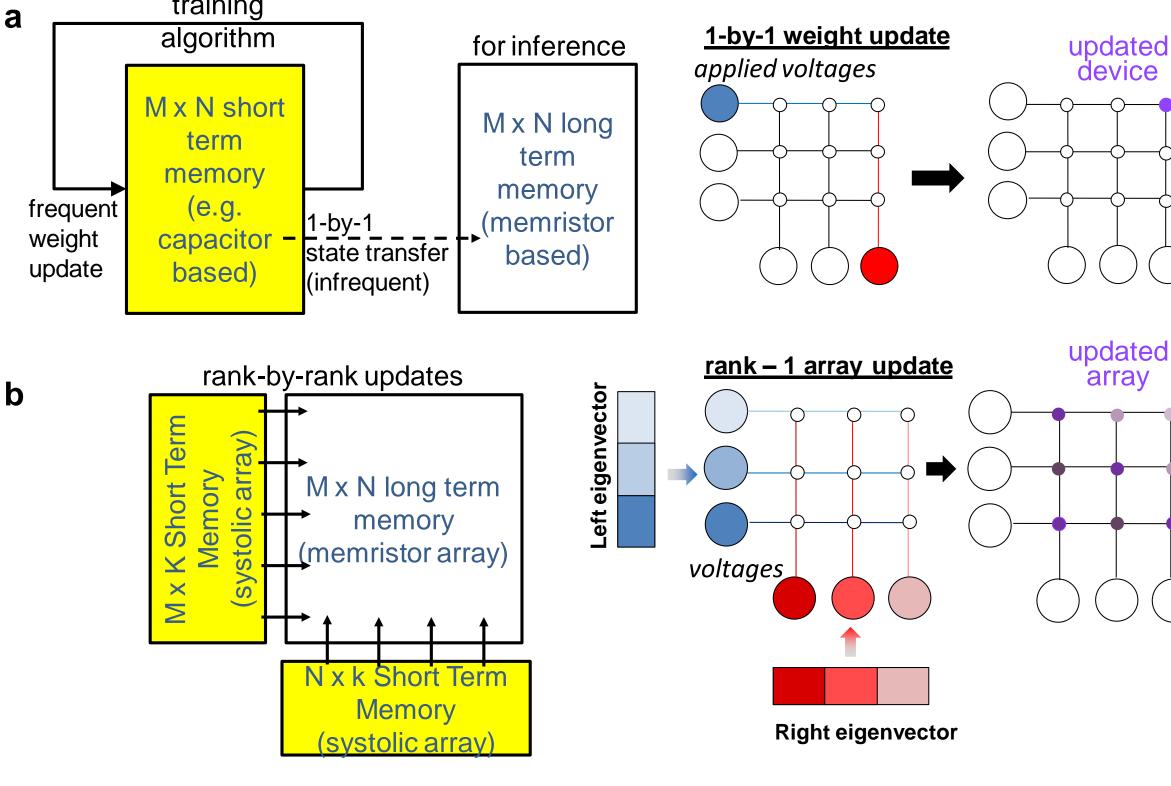


Figure 1. Existing vs. proposed approach to training memristor M x N arrays (a) Duplicative short-term memory (M x N capacitor array) overcomes memristor non-ideality and the high programming power of 1-by-1 weight updating [2]; (b) proposed approach with low rank short term memory implemented using systolic arrays that produces rank-by-rank updates at the array level. "Author's Own"

Relevance to FRANC: Efficient **digital coprocessors** can improve the **technology readiness level** of emerging technologies: • Exploit new technologies for **inference** to use in **training** • Mitigate device limitations, reduce AI operation energy • bring edge performance to the warfighter.

EigenArch: A Low Rank Hardware Machine Learning Accelerator Gina Adam Brian Hoskins Martin Lueker-Boden George Washington University NIST Gaithersburg Western Digital Research

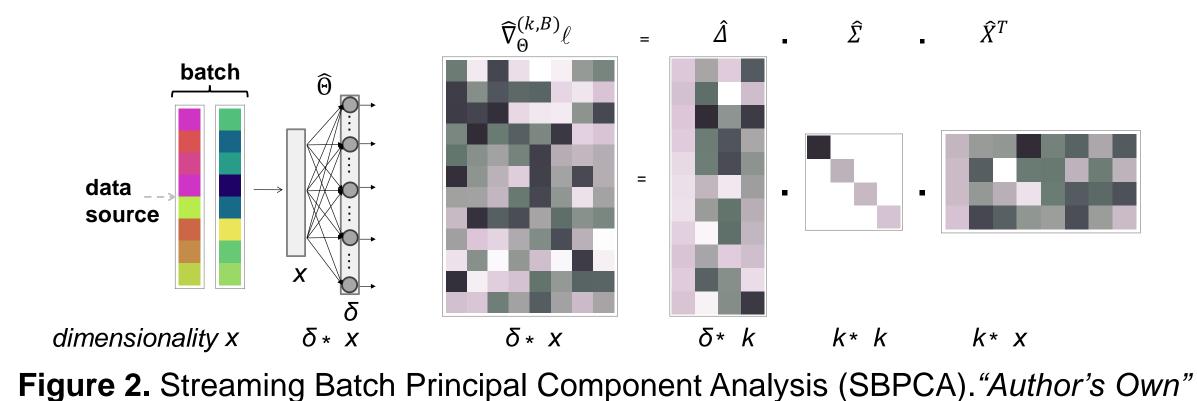
Approach

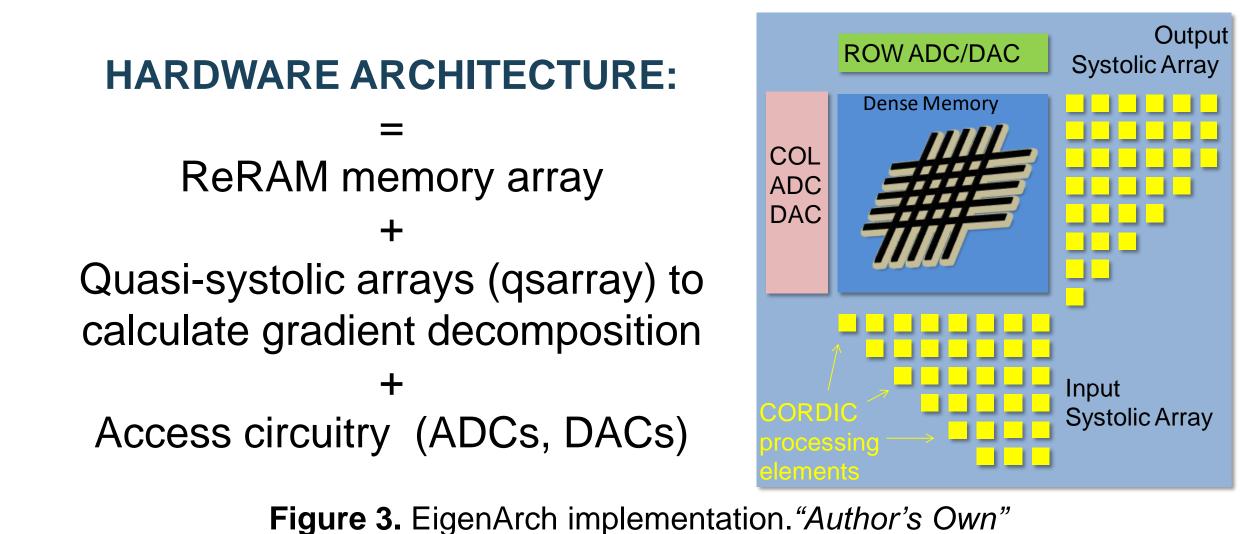
Our EigenArch is based on three interconnected tasks:

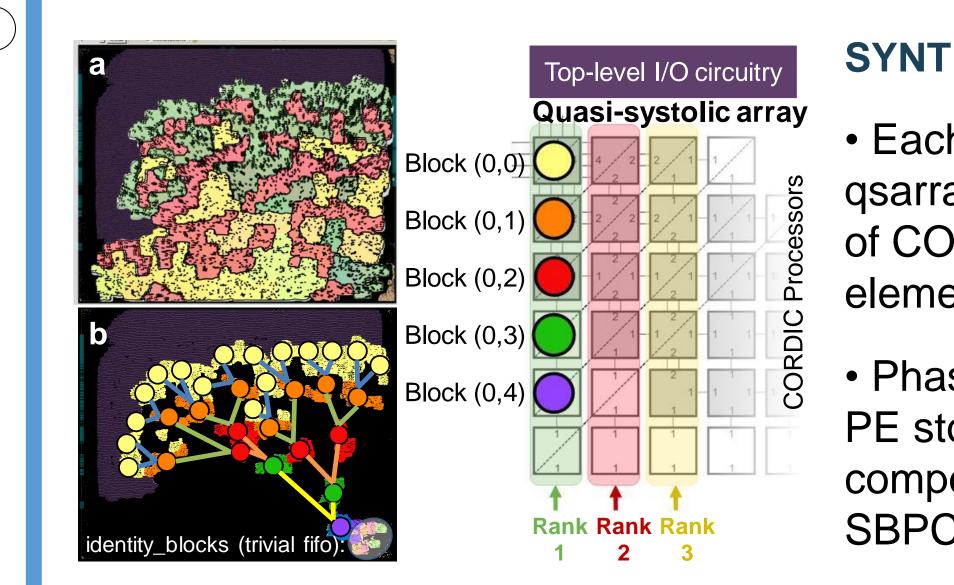
- 1) Algorithms to approximate gradient data in machine **learning efficiently.** We proposed streaming batch principal component analysis (SBPCA) [4] (Fig. 2).
- 2) Compact hardware implementations. We proposed and synthesized quasi-systolic array (QSArray) (Figs. 3 and 4).
- 3) Experimental validation in 20,000 ReRAM device platform

ALGORITHMIC IMPLEMENTATION:

SBPCA = approximation of a full gradient matrix from k-rank samples of its contributed parts







SYNTHESIS RESULTS:

• Each column in the qsarray is a binary tree of CORDIC processing elements (PE)

• Phase angles in each PE store the principal components for the SBPCA algorithm.

Figure 4. Synthesis results (a) rank-level maps for a rank-3 quasi-systolic array with 128-element Input Vectors in a TSMC 16nm process, meets timing of 500 MHz. (b) hypothetical visualization of the binary tree for rank 1. "Author's Own"

This research was developed with funding from the Defense Advanced Research Projects Agency (DARPA). The views, opinions and/or findings expressed are those of the author and should not be interpreted as representing the official views or policies of the Department of Defense or the U.S. Government. Distribution Statement A – Approved for Public Release, Distribution Unlimited

Artificial Intelligence

Results and Impact

The results obtained in the first six months are:

1) Proposed SBPCA algorithm approximates well gradient data for training on datasets of various complexities e.g. CIFAR-10, CIFAR-100 (Fig. 5)

• Comparable accuracy at low rank to traditional minibatch gradient descent (MBGD) at **lower memory**

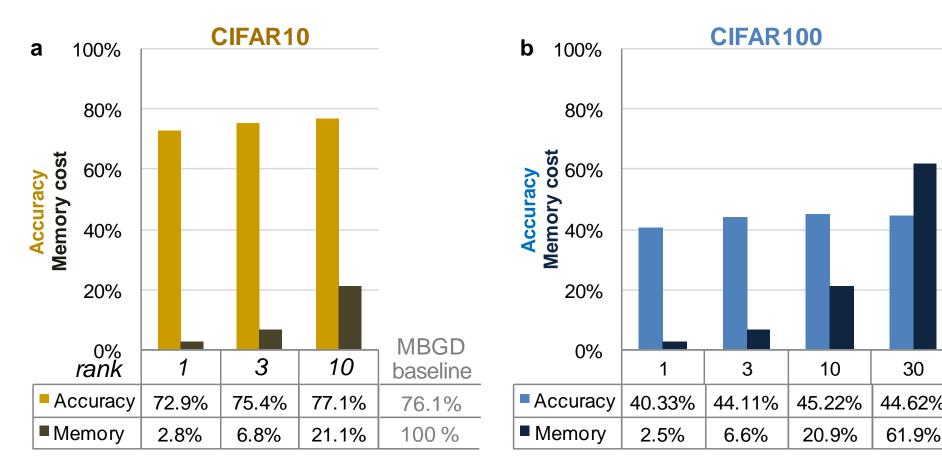


Figure 5. SBPCA accuracy and memory results. For low rank decomposed form has similar accuracy with MBGD for (a) CIFAR10 and (b) CIFAR100. "Author's Own"

2) Systolic hardware implementation has good performance with higher technology readiness (Fig. 6):

 Area/energy/latency estimates obtained by synthesis of Verilog code in Synopsys Design Compiler

| Existing technologies | | | | EigenArc | |
|--|------------------------|--|-----------------------|--|-----------|
| Google: TPU TSMC 28nm Digital, 8 Bit | | IBM: 3T1C+PCM* 90 nm Analog, 8 bit | | NIST\WD\G\ QSARRAY: 512, TSMC 16nm Digit | |
| Property | Metric | Property | Metric | Property | |
| Energy VMM Forward (Back) | 456 (912) nJ | VMM Forward (Back) | 12.51 (25.22) nJ | Energy/Example Left (Right) | 8.6 |
| Array Latency | 3000 ns | VMM Latency (Back)* | 26.7 (53.4)ns | | |
| | | Area | 5.8 mm ² | Array Latency | 24 |
| Pipeline Latency | 3ns | Transfer Energy | 22894 nJ | Pipeline Latency | 12 |
| Area (MAC Only)* | 317.76 mm ² | TE/Example (8000) | 2.87 nJ | Area Left (Right) | 1.(mi |
| Technology readiness | Operational | Technology readiness | Lower | Technology readiness | Hi |
| *original TPU is 256×256 MAC *Energy and area: ~60% capacitors + ~40% PCN *For 3 layer network, total latency ~240 ns | | | *projected from model | | |

*For 3 layer network, total latency ~240 ns

Figure 6. Performance estimates and comparisons "Author's Own"

Impact for DoD and commercial efforts:

Increases technology readiness level of ReRAM for AI

- Proposed systolic implementation in existing technology
- \rightarrow quick prototyping for DoD and commercialization
- Applicable beyond ReRAM to other analog technologies

[1] Y. Gao, S. Wu, G.C. Adam, accepted ICONS 2020. **References** ^[2] S. Ambrogio et al., Nature, 558, 7708, 2018. [3] F. Vanpoucke, M. Moonen, E. Deprettere, TCAS II, 44(3), 253-256, 1997. [4] S. Huang, B. D.Hoskins, M. W. Daniels, M. Stiles, G.C. Adam, AAAI 2020.



